James T. Teherani



Columbia University
Assistant Professor, Department of Electrical Engineering
500 West 120th Street, Room 1300
New York, New York 10027

16 students; student evaluations: course 4.94/5, instructor 4.75/5

24 students; student evaluations: course 4.13/5, instructor 4.50/5

ELEN E3106: Solid-state Devices and Materials (taught with Prof. Kymissis)

214.435.9761 (cell) j.teherani@columbia.edu http://teherani.ee.columbia.edu

Fall 2015

Updated March 2020

Field	d of	speci	aliza	ition
		3 P C C.	a	

semiconductor device physics;

modeling, simulation, and nanoscale fabrication of electronic devices built from 2D materials

modeling, simulation, and handscale labilitation of electronic devices saint from 25 materials	
Education ————————————————————————————————————	
Massachusetts Institute of Technology GPA 5.0/5.0 PhD Electrical Engineering and Computer Science Thesis: Fundamental Limits of the Switching Abruptness of Tunneling Transistors Advisors: Prof. Judy Hoyt and Prof. Dimitri Antoniadis	2015
S.M. Electrical Engineering and Computer Science Thesis: <i>Band-to-band Tunneling in Silicon Diodes and Tunnel Transistors</i> Advisors: Prof. Judy Hoyt and Prof. Dimitri Antoniadis	2010
The University of Texas at Austin GPA 4.0/4.0	
B.S. Electrical and Computer Engineering, Highest Honors	2008
Professional Experience —	
Columbia University Assistant Professor in the Department of Electrical Engineering	2015 – present
MIT Department of Electrical Engineering and Computer Science Postdoctoral associate. Advisor: Prof. Antoniadis	2015
MIT Department of Electrical Engineering and Computer Science Semiconductor device physics graduate researcher. Advisors: Prof. Hoyt and Prof. Antoniadis	2008 – 2015
IBM Research , T. J. Watson Research Center, Yorktown Heights, New York <i>Device physics intern</i> . Advisor: Dr. Paul Solomon	2009
DRS Infrared Technologies, Dallas, Texas Engineering intern. Advisor: Jeffrey Beck	2005, 2007
Courses Taught	
ELEN E4301: Introduction to Semiconductor Devices	Fall 2015

Electrical Engineering Lab for ENGI E1102: The Art of Engineering 30 students; student evaluations unavailable	Fall 2015
Electrical Engineering Lab for ENGI E1102: The Art of Engineering 30 students; student evaluations: course 4.08/5, instructor 4.67/5	Spring 2016
ELEN E4301: Introduction to Semiconductor Devices 44 students; student evaluations: course 4.69/5, instructor 4.85/5	Fall 2016
ELEN E9301: Topics: Theory and Practice of Device Scaling (taught with Prof. Theis) 25 students; student evaluations: course 4.94/5, instructor 4.92/5	Spring 2017
ELEN E6333: Semiconductor Device Physics 12 students; student evaluations: course 4.93/5, instructor 5.00/5	Fall 2017
ELEN E3106: Solid-state Devices and Materials 37 students; student evaluations: course 3.95/5, instructor 4.05/5	Fall 2018
ELEN E6333: Semiconductor Device Physics 12 students; student evaluations: course 4.63/5, instructor 4.63/5	Fall 2018
ELEN E6333: Semiconductor Device Physics 17 students; student evaluations: course 4.54/5, instructor 4.62/5	Fall 2019
ELEN E6903: Topics: Nanoelectronic Device Simulations (taught with Prof. Ramirez) 11 students; student evaluations: course 3.43/5, instructor 3.67/5	Fall 2019
Supervised Research ————————————————————————————————————	
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Supervised Research MS/PhD Xinyi Xu (co-advised with P. J. Schuck)	2018 – 2019
MS/PhD Xinyi Xu (co-advised with P. J. Schuck) Abhinandan Borah, Modeling Charge in Low DOS Systems	2016 – present
MS/PhD Xinyi Xu (co-advised with P. J. Schuck) Abhinandan Borah, Modeling Charge in Low DOS Systems Ankur Nipane, Electrostatics of Low Dimensional Junctions	2016 – present 2016 – present
MS/PhD Xinyi Xu (co-advised with P. J. Schuck) Abhinandan Borah, Modeling Charge in Low DOS Systems	2016 – present
MS/PhD Xinyi Xu (co-advised with P. J. Schuck) Abhinandan Borah, Modeling Charge in Low DOS Systems Ankur Nipane, Electrostatics of Low Dimensional Junctions	2016 – present 2016 – present
MS/PhD Xinyi Xu (co-advised with P. J. Schuck) Abhinandan Borah, Modeling Charge in Low DOS Systems Ankur Nipane, Electrostatics of Low Dimensional Junctions Anjaly Thekkevilayil Rajendran (co-advised with J. Hone)	2016 – present 2016 – present
MS/PhD Xinyi Xu (co-advised with P. J. Schuck) Abhinandan Borah, Modeling Charge in Low DOS Systems Ankur Nipane, Electrostatics of Low Dimensional Junctions Anjaly Thekkevilayil Rajendran (co-advised with J. Hone) Postdoctoral Associates	2016 – present 2016 – present 2019 – present 2016 – 2019 2017 – present
MS/PhD Xinyi Xu (co-advised with P. J. Schuck) Abhinandan Borah, Modeling Charge in Low DOS Systems Ankur Nipane, Electrostatics of Low Dimensional Junctions Anjaly Thekkevilayil Rajendran (co-advised with J. Hone) Postdoctoral Associates Younghun Jung (co-advised with Prof. Hone)	2016 – present 2016 – present 2019 – present 2016 – 2019
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MS/PhD Xinyi Xu (co-advised with P. J. Schuck) Abhinandan Borah, Modeling Charge in Low DOS Systems Ankur Nipane, Electrostatics of Low Dimensional Junctions Anjaly Thekkevilayil Rajendran (co-advised with J. Hone) Postdoctoral Associates Younghun Jung (co-advised with Prof. Hone) Minsup Choi (co-advised with Prof. Hone) Yang Liu (co-advised with Prof. Hone) MS Sirisha Jayanti, Calculation of Potential Across Non-ideal PN Junctions Tian Sun, Large Field Electromagnet for Electronic Test Set Punnu Jose Sebastian, Fabrication of Encapsulated van der Waals Structures Jiazhang Wang, Modular Probe Station for Quick Device Assessment	2016 – present 2016 – present 2019 – present 2016 – 2019 2017 – present 2017 2017 2017 2017 2017 – 2018 2018 – 2019
MS/PhD Xinyi Xu (co-advised with P. J. Schuck) Abhinandan Borah, Modeling Charge in Low DOS Systems Ankur Nipane, Electrostatics of Low Dimensional Junctions Anjaly Thekkevilayil Rajendran (co-advised with J. Hone) Postdoctoral Associates Younghun Jung (co-advised with Prof. Hone) Minsup Choi (co-advised with Prof. Hone) Yang Liu (co-advised with Prof. Hone) MS Sirisha Jayanti, Calculation of Potential Across Non-ideal PN Junctions Tian Sun, Large Field Electromagnet for Electronic Test Set Punnu Jose Sebastian, Fabrication of Encapsulated van der Waals Structures	2016 – present 2016 – present 2019 – present 2016 – 2019 2017 – present 2019 – present 2017 2017 2017
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Joshua Polanco Calderon, sophomore, Columbia SEAS Leslie Ortiz, junior, Barnard Physics Andrew Murphy, senior, Columbia Physics Alice Wu, junior, Columbia Electrical Engineering Zhenguo Wu, junior, Columbia Electrical Engineering Adina Bechhofer, junior, Columbia Electrical Engineering	2018 2018 2018 – 2019 2018 – 2019 2018 – present
Visiting students Rui Ding, undergraduate from University of Science and Technology of China Jiayue Li, MS student from Nanjing University Marco Fratus, MS student from KTH Sweden/Politecnico di Milano Yefei Zhang, MS/PhD student from Xi'an Jiaotong University Myeongjun Lee, visiting PhD student from SKKU, Korea	2016 2016 – 2017 2016 – 2018 2016 – 2018 2019
Thesis Committees —	
Committee member Tarun Chari, PhD in Electrical Engineering Optimization Studies in Graphene Electronics	2016
Daniel Chenet, PhD in Mechanical Engineering 2D Materials: Synthesis, Characterization, and Applications, joined Intel	2016
Amrita Masurkar, PhD in Electrical Engineering Charge Injection and Transport in Pentacene Field-Effect Transistors	2016
Hyungsik Kim, PhD in Electrical Engineering Unconventional CVD Graphene and α -MoO3 Electronics for Very Large Scale Integration (VLSI)	2017
Scott Trocchia, PhD in Electrical Engineering Single-molecule Carbon Nanotube Field-effect Transistors for Genomic Applications	2017
Charishma Puliyanda Subbaiah, PhD in Electrical Engineering Electrically Driven Ion Pumping in a Single-walled Carbon Nanotube	2018
Cheng Tan, PhD in Electrical Engineering Gate Tunable Transport in Hexagonal Boron Nitride Encapsulated Bilayer Graphene	2019
Changjian Julia Zhang, PhD in Mechanical Engineering Engineering and Probing Two-dimensional Materials and Heterostructures	2020
Peijie Ong, PhD in Applied Physics and Applied Mathematics Optimization and characterization of noise in ion channel and carbon nanotube biosensing platf	2020 forms

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Publications -

(by convention, PI is typically listed last)

Papers in Refereed Journals

- J1. H. F. Schaake, M. A. Kinch, D. Chandra, F. Aqariden, P. K. Liao, D. F. Weirauch, C.-F. Wan, R. E. Scritchfield, W. W. Sullivan, J. T. Teherani, and H. D. Shih, "High-Operating-Temperature MWIR Detector Diodes," *Journal of Elec Materi*, vol. 37, no. 9, pp. 1401–1405, Sep. 2008. https://doi.org/10.1007/s11664-008-0423-6
- J. Beck, R. Scritchfield, B. Sullivan, J. T. Teherani, C.-F. Wan, M. Kinch, M. Ohlson, M. Skokan, L. Wood, P. Mitra, M. Goodwin, and J. Robinson, "Performance and Modeling of the MWIR HgCdTe Electron Avalanche Photodiode," *Journal of Elec Materi*, vol. 38, no. 8, pp. 1579–1592, Aug. 2009. https://doi.org/10.1007/s11664-009-0684-8
- J3. P. M. Solomon, I. Lauer, A. Majumdar, J. T. Teherani, M. Luisier, J. Cai, and S. J. Koester, "Effect of Uniaxial Strain on the Drain Current of a Heterojunction Tunneling Field-Effect Transistor," *Electron Device Letters, IEEE*, vol. 32, no. 4, pp. 464–466, 2011. https://doi.org/10.1109/LED.2011.2108993
- J4. P. Hashemi, W. Chern, H. Lee, J. T. Teherani, Y. Zhu, J. Gonsalvez, G. G. Shahidi, and J. L. Hoyt, "Ultrathin Strained-Ge Channel P-MOSFETs With High-K/Metal Gate and Sub-1-nm Equivalent Oxide Thickness," *IEEE Electron Device Letters*, vol. 33, no. 7, pp. 943–945, Jul. 2012. https://doi.org/10.1109/LED.2012.2195631
- J. T. Teherani, W. Chern, D. A. Antoniadis, J. L. Hoyt, L. Ruiz, C. D. Poweleit, and J. Menéndez, "Extraction of large valence-band energy offsets and comparison to theoretical values for strained-Si/strained-Ge type-II heterostructures on relaxed SiGe substrates," *Phys. Rev. B*, vol. 85, no. 20, p. 205308, May 2012. https://doi.org/10.1103/PhysRevB.85.205308
- J. T. Teherani, S. Agarwal, E. Yablonovitch, J. L. Hoyt, and D. A. Antoniadis, "Impact of Quantization Energy and Gate Leakage in Bilayer Tunneling Transistors," *IEEE Electron Device Letters*, vol. 34, no. 2, pp. 298–300, Feb. 2013. https://doi.org/10.1109/LED.2012.2229458
- J7. T. Yu, J. T. Teherani, D. A. Antoniadis, and J. L. Hoyt, "InGaAs/GaAsSb Quantum-Well Tunnel-FETs With Tunable Backward Diode Characteristics," *IEEE Electron Device Letters*, vol. 34, no. 12, pp. 1503–1505, 2013. https://doi.org/10.1109/LED.2013.2287237
- J8. S. Agarwal, J. T. Teherani, J. L. Hoyt, D. A. Antoniadis, and E. Yablonovitch, "Engineering the Electron-Hole Bilayer Tunneling Field-Effect Transistor," *IEEE Transactions on Electron Devices*, vol. 61, no. 5, pp. 1599–1606, May 2014. https://doi.org/10.1109/TED.2014.2312939
- J9. W. Chern, P. Hashemi, J. T. Teherani, D. A. Antoniadis, and J. L. Hoyt, "Record Hole Mobility at High Vertical Fields in Planar Strained Germanium on Insulator With Asymmetric Strain," *IEEE Electron Device Letters*, vol. 35, no. 3, pp. 309–311, Mar. 2014. https://doi.org/10.1109/LED.2014.2300197
- J10. J. T. Teherani, W. Chern, D. A. Antoniadis, and J. L. Hoyt, "Ultra-Thin, High Quality HfO2 on Strained-Ge MOS Capacitors with Low Leakage Current," *ECS Trans.*, vol. 64, no. 6, pp. 267–271, Aug. 2014. https://doi.org/10.1149/06406.0267ecst

- J11. T. Yu, J. T. Teherani, D. A. Antoniadis, and J. L. Hoyt, "Effects of substrate leakage and drain-side thermal barriers in In0.53Ga0.47As/GaAs0.5Sb0.5 quantum-well tunneling field-effect transistors," *Appl. Phys. Express*, vol. 7, no. 9, p. 094201, Sep. 2014. https://doi.org/10.7567/APEX.7.094201
- J. T. Teherani, S. Agarwal, W. Chern, P. M. Solomon, E. Yablonovitch, and D. A. Antoniadis, "Auger generation as an intrinsic limit to tunneling field-effect transistor performance," *Journal of Applied Physics*, vol. 120, no. 8, p. 084507, Aug. 2016. https://doi.org/10.1063/1.4960571
- J13. A. Kerelsky, A. Nipane, D. Edelberg, D. Wang, X. Zhou, A. Motmaendadgar, H. Gao, S. Xie, K. Kang, J. Park, J. T. Teherani, and A. Pasupathy, "Absence of a Band Gap at the Interface of a Metal and Highly Doped Monolayer MoS2," *Nano Lett.*, Sep. 2017. https://doi.org/10.1021/acs.nanolett.7b01986
- J14. A. Nipane, S. Jayanti, A. Borah, and J. T. Teherani, "Electrostatics of lateral p-n junctions in atomically thin materials," *Journal of Applied Physics*, vol. 122, no. 19, p. 194501, Nov. 2017. https://doi.org/10.1063/1.4994047
- J. T. Teherani, "A Comprehensive Theoretical Analysis of Hole Ballistic Velocity in Si, SiGe, and Ge: Effect of Uniaxial Strain, Crystallographic Orientation, Body Thickness, and Gate Architecture," *IEEE Transactions on Electron Devices*, vol. 64, no. 8, pp. 3316–3323, Aug. 2017. https://doi.org/10.1109/TED.2017.2708691
- J16. A. Borah, P. J. Sebastian, A. Nipane, and J. T. Teherani, "An Intuitive Equivalent Circuit Model for Multilayer Van Der Waals Heterostructures," *IEEE Transactions on Electron Devices*, vol. 65, no. 10, pp. 4209–4215, Oct. 2018. https://doi.org/10.1109/TED.2018.2851920
- J17. A. Nipane, S. Jayanti, A. Borah, and J. T. Teherani, "Erratum: 'Electrostatics of lateral p-n junctions in atomically thin materials,'" *Journal of Applied Physics*, vol. 124, no. 13, p. 139902, Oct. 2018. https://doi.org/10.1063/1.5051548
- J18. A. Nipane, Y. Zhang, and J. T. Teherani, "Role of out-of-plane dielectric thickness in the electrostatic simulation of atomically thin lateral junctions," *Journal of Applied Physics*, vol. 123, no. 21, p. 214302, Jun. 2018. https://doi.org/10.1063/1.5027520
- J19. Y. Jung, M. S. Choi, A. Nipane, A. Borah, B. Kim, A. Zangiabadi, T. Taniguchi, K. Watanabe, W. J. Yoo, J. Hone, and J. T. Teherani, "Transferred via contacts as a platform for ideal two-dimensional transistors," *Nature Electronics*, vol. 2, no. 5, p. 187, May 2019. https://doi.org/10.1038/s41928-019-0245-y
- J20. I. Moon, S. Lee, M. Lee, C. Kim, D. Seol, Y. Kim, K. Hyun Kim, G. Young Yeom, J. T. Teherani, J. Hone, and W. Jong Yoo, "The device level modulation of carrier transport in a 2D WSe 2 field effect transistor via a plasma treatment," *Nanoscale*, vol. 11, no. 37, pp. 17368–17375, 2019. https://doi.org/10.1039/C9NR05881H

Proceedings of Refereed Conferences

C1. J. Beck, R. Scritchfield, B. Sullivan, J. T. Teherani, C.-F. Wan, M. Kinch, M. Ohlson, M. Skokan, L. Wood, P. Mitra, M. Goodwin, and J. Robinson, "Performance and modeling of the MWIR HgCdTe electron

- avalanche photodiode," *Proceedings of the SPIE*, 2009, vol. 7298, pp. 729838–729838–17. https://doi.org/10.1117/12.819045
- C2. P. Hashemi, J. T. Teherani, and J. L. Hoyt, "Investigation of hole mobility in gate-all-around Si nanowire p-MOSFETs with high-K/metal-gate: Effects of hydrogen thermal annealing and nanowire shape," *IEEE International Electron Devices Meeting (IEDM)*, 2010, pp. 34.5.1-34.5.4. https://doi.org/10.1109/IEDM.2010.5703477
- C3. W. Chern, P. Hashemi, J. T. Teherani, T. Yu, Y. Dong, G. Xia, D. A. Antoniadis, and J. L. Hoyt, "High mobility high-K-all-around asymmetrically-strained Germanium nanowire trigate p-MOSFETs," *IEEE International Electron Devices Meeting (IEDM)*, 2012, pp. 16.5.1-16.5.4. https://doi.org/10.1109/IEDM.2012.6479055
- C4. S. Agarwal, J. T. Teherani, J. L. Hoyt, D. A. Antoniadis, and E. Yablonovitch, "Optimization of the electron hole bilayer tunneling field effect transistor," *71st Device Research Conference (DRC)*, 2013, pp. 109–110. https://doi.org/10.1109/DRC.2013.6633817
- C5. J. T. Teherani, W. Chern, D. A. Antoniadis, and J. L. Hoyt, "Simulation of enhanced hole ballistic velocity in asymmetrically strained Germanium nanowire trigate p-MOSFETs," *IEEE International Electron Devices Meeting (IEDM)*, 2013, pp. 32.4.1-32.4.4. https://doi.org/10.1109/IEDM.2013.6724737
- C6. J. T. Teherani, T. Yu, D. A. Antoniadis, and J. L. Hoyt, "Electrostatic design of vertical tunneling field-effect transistors," *Third Berkeley Symposium on Energy Efficient Electronic Systems (E3S)*, 2013, pp. 1–2. https://doi.org/10.1109/E3S.2013.6705872
- C7. J. T. Teherani, W. Chern, S. Agarwal, J. L. Hoyt, and D. A. Antoniadis, "A framework for generation and recombination in tunneling field-effect transistors," *Fourth Berkeley Symposium on Energy Efficient Electronic Systems (E3S)*, 2015, pp. 1–3. https://doi.org/10.1109/E3S.2015.7336797
- C8. A. Kerelsky, A. Nipane, D. Edelberg, D. Wang, M. Cheng, A. Dadgar, H. Gao, K. Kang, J. Park, J. T. Teherani, and A. Pasupathy, "Band Structure Evolution in Vertically Contacted MoS2 Probed Using Scanning Tunneling Spectroscopy," *Bulletin of the American Physical Society*, New Orleans, Louisiana, 2017, vol. Volume 62, Number 4. http://meetings.aps.org/Meeting/MAR17/Session/L32.12
- C9. M. S. Choi, Y. Jung, D. Rhodes, B. Kim, J. T. Teherani, J. Hone, and W. J. Yoo, "Study of Contact Properties for Semiconducting TMDCs Using Via Contacts Embedded in h-BN," *Bulletin of the American Physical Society*, Los Angeles, California, 2018. http://meetings.aps.org/Meeting/MAR18/Session/T60.169
- C10. Y. Jung, M. S. Choi, A. Borah, A. Nipane, W. J. Yoo, J. Hone, and J. T. Teherani, "Reliable High-Quality Metal-Embedded h-BN Contacts to p-type WSe2," *76th Device Research Conference (DRC)*, 2018, pp. 1–2. https://doi.org/10.1109/DRC.2018.8442181
- C11. J. T. Teherani, "The Auger FET: a Novel Device Concept for Subthermal Switching," *IEEE 2nd Electron Devices Technology and Manufacturing Conference (EDTM)*, 2018, pp. 208–210. https://doi.org/10.1109/EDTM.2018.8421442

- C12. J. T. Teherani, "Orientation Dependence of the Hole Ballistic Velocity in Si, SiGe, and Ge Thin-Body Structures with Uniaxial Compressive Strain," *ECS Fall Meeting*, Cancun, Mexico, 2018, vol. MA2018-02, pp. 1017–1017. http://ma.ecsdl.org/content/MA2018-02/31/1017
- C13. A. Nipane, P. J. Sebastian, Y. Jung, M. S. Choi, A. Borah, W. J. Yoo, J. Hone, and J. T. Teherani, "Atomic Layer Etching (ALE) of WSe2 Yielding High Mobility p-FETs," 2019 Device Research Conference (DRC), 2019, pp. 231–232. https://doi.org/10.1109/DRC46940.2019.9046402

Other Major Publications

- MP1. J. T. Teherani, "Band-to-band tunneling in silicon diodes and tunnel transistors," Thesis, MIT, Cambridge, MA, USA, 2010. https://doi.org/1721.1/60215
- MP2. J. T. Teherani, "TEM Lattice Calculator," nanohub.org, 2013. https://doi.org/10.4231/D3VQ2S96B
- MP3. J. T. Teherani and J. L. Hoyt, "A Physically-Intuitive Method for Calculation of the Local Lattice Constant from a High-Resolution Transmission Electron Microscopy Image by Fourier Analysis," arXiv, Sep. 2013. http://arxiv.org/abs/1309.3155
- MP4. J. T. Teherani, "Uniaxial and Biaxial Stress/Strain Calculator for Semiconductors," *nanohub.org*, 2014. https://doi.org/10.4231/D33F4KN4J
- MP5. J. T. Teherani, "How Computers Compute," YouTube, 2014. https://youtu.be/8cVsgFN3hSM
- MP6. J. T. Teherani, "What is a Semiconductor?" YouTube, 2015. https://youtu.be/gUmDVe6C-BU
- MP7. J. T. Teherani, "Fundamental limits of the switching abruptness of tunneling transistors," Thesis, Massachusetts Institute of Technology, 2015. https://doi.org/1721.1/99853
- MP8. A. Borah and J. T. Teherani, "Electrostatic Properties Simulation of Layered 2D Material Devices," nanohub.org, 2017. https://doi.org/10.21981/D3C24QQ39
- MP9. J. T. Teherani, "Building at the Nanoscale | Part 01: 2D vs 3D Materials," YouTube, 2019. https://youtu.be/4m-1vxXQHtY
- MP10. J. T. Teherani, "Building at the Nanoscale | Part 02: How to Build 2D Atomic Stacks," *YouTube*, 2019. https://youtu.be/JgfkLhMo1fA

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Grants -

Current

Sponsor National Science Foundation

Title MRSEC: Columbia Center for Precision Assembly of Superstratic and Superatomic Solids

Lead PI J. Hone (Columbia University)

Total Amount \$15,791,022

Award Period 11/1/2014 — 10/31/2020 Location Columbia Nano Initiative (CNI)

Sponsor National Science Foundation

Title CAREER: Exploiting Many-Particle Physics for Low-Energy Nanoelectronics

Lead PI J. Teherani (Columbia University)

Total Amount \$508,000

Award Period 2/15/2018 — 1/31/2023 Location Columbia Nano Initiative (CNI)

Sponsor National Science Foundation

Title Collaborative Research: REU Site: Nano-NY

Lead PI I. Kymissis (Columbia University)

Total Amount \$372,997

Award Period 4/1/2018 — 3/31/2020

Location Columbia Nano Initiative (CNI)

Pending

Sponsor National Science Foundation

Title Collaborative Research: REU Site: Nano-NY

Lead PI I. Kymissis (Columbia University)

Total Amount \$398,853

Award Period 4/1/2020 - 3/31/2023

Location Columbia Nano Initiative (CNI)

Sponsor National Science Foundation

Title Columbia University MRSEC on Precision-Assembled Quantum Materials

Lead PI J. Hone (Columbia University)

Total Amount \$15,600,000

Award Period 9/1/2020 – 8/31/2026

Location Columbia Nano Initiative (CNI)

Awards and Honors -

University of Texas, Engineering Foundation Undergraduate Endowed Presidential Scholarship National Nanotechnology Infrastructure Network (NNIN) International Winter School Fellow	2007 2011
Purdue University, Network for Computation Nanotechnology Summer School Scholarship	2011
National Defense Science and Engineering Graduate Fellowship (NDSEG) 20	010 – 2013
George E. Smith Award (best paper in IEEE Electron Device Letters journal)	2014
NSF Center for Energy Efficient Electronics Science Leadership Award	2014
National Science Foundation Graduate Fellowship 20	010 – 2015
Edward and Carole Kim Faculty Involvement Award — for excellent teaching and service to student	s 2018
National Science Foundation CAREER Award	2018
Invited Talks —	
University of Notre Dame	2016
Auger Generation as a Fundamental Limit to the Off-state of TFETs	
Purdue University	2016
Auger generation as an intrinsic limit to tunneling field-effect transistor performance	
DRS Infrared Technologies Auger generation as an intrinsic limit to tunneling field-effect transistor performance	2016
IBM T. J. Watson Research Center Auger generation as an intrinsic limit to tunneling field-effect transistor performance	2016
Steep Slope Workshop at École Polytechnique Fédérale de Lausanne Auger generation as an intrinsic limit to tunneling field-effect transistor performance	2016
Massachusetts Institute of Technology, Microsystems Tech. Annual Research Conference Opportunities after Graduate School	2017
University of Texas at Austin Auger generation as an intrinsic limit to tunneling field-effect transistor performance	2017
2018 IEEE Electron Devices Technology and Manufacturing (EDTM) Conference The Auger FET: a Novel Device Concept for Subthermal Switching	2018
The 27 th Connecticut Symposium on Microelectronics & Optoelectronics (CMOC) The Unique Electrostatics of Vertical Junctions to 2D Materials	2018
IEEE 2nd Electron Devices Technology and Manufacturing Conference (EDTM) The Auger FET: a Novel Device Concept for Subthermal Switching	2018
The Electrochemical Society Fall Meeting Orientation Dependence of the Hole Ballistic Velocity in Si, SiGe, and Ge Thin-Body Structures with Compressive Strain	2018 Jniaxial
IEEE S3S (SOI-3D-Subthreshold) Microelectronics Technology Unified Conference Optimization of Intrinsic Auger-Assisted Tunneling of TFETs with Steep Subthreshold Slopes	2018
USC Department of Electrical Engineering Auger Generation as an Intrinsic Mechanism Limiting Tunneling Field-Effect Transistor Performance	2018

The 7th SKKU Workshop on Materials Frontier Research (Topics on Atomically Engineered Materials and Processing) Transferred via contacts as a device platform for ideal 2D transistors	2019
Graphene for US Conference New techniques for doping and contacts to 2D materials	2020
Service ————	
University Service	
Faculty Advisor, Columbia University Society of Women Engineers (SWE)	2016 – present
Faculty Advisor, Columbia University Amateur Radio Club	2018 – present
Faculty Advisor, Columbia University Society of Hispanic Professional Engineers (SHPE)	2018 – present
Department of Electrical Engineering Undergraduate Committee	2015 – present
Department of Electrical Engineering Curriculum Committee	2018 – present
Department of Electrical Engineering ABET Committee	2018 – present
Department of Electrical Engineering Undergraduate Advising Committee Chair	2018 – present
Department of Electrical Engineering PhD Defense Qualifying Exam (DQE) Committee	2018 – present
Department of Electrical Engineering Distinguished Lectures Committee	2018 – 2019
Service to the Discipline	
Editor, IEEE Transactions on Electron Devices	2017 – 2018
Special Issue on 2D Materials for Electronic, Optoelectronic and Sensor Devices	
Review Panelist, Department of Defense National Defense Science and Engineering Graduate (NDSEG) Fellowship	2017 – 2019
Nanotechnology Committee Member, IEEE Electron Device Society (EDS)	2017 – present
Technical Program Committee Member, Device Research Conference	2018 – present
Public Outreach	
Educational Outreach Video, Building at the Nanoscale: Part 01, 2D and 3D materials	2019
Educational Outreach Video, <u>Building at the Nanoscale: Part 02</u> , how to build structures f thin 2D materials	from atomically 2019
Outreach talk on graduate school opportunities to the Society of Hispanic Engineers	2019
Lab tour and outreach seminar to 50 students from Corpus Christi school (7th and 8th grad	ders) 2019
Seminar on "Graduate Education and Careers" to annual EngAGE program, which targets prograduate students from underrepresented backgrounds	prospective 2019
Girl Scouts lab tour and outreach seminar through the Society of Women Engineers (midd	le school) 2018
Summer@SEAS seminar on life beyond undergraduate education	2018
MRSEC REU Seminar, "What is Grad School All About?"	2018
STEM workshop for students from the Bronx Center for Science and Mathematics	2018

Columbia Engineering Outreach Programs, Inside Engineering	
Central Park East II, Manhattan, New York	2018
Mott Hall II Middle School, Manhattan, New York	2018
John Ericsson Middle School, Brooklyn, New York	2018
Mott Hall II Middle School, Manhattan, New York	2017
Mott Hall II Middle School, Manhattan, New York (second visit)	2017
Scholars' Academy, Queens, New York	2016
Lower East Side Preparatory High School, Manhattan, New York	2016
Mott Hall II Middle School, Manhattan, New York Bayside High School, Bronx, New York	2016 2016
MakeCU Hardware Hackathon, Faculty Judge	2010
SAT Physics Workshop for Students from <i>Bronx Center for Science and Mathematics</i>	2018
Columbia Engineering Achievers in Graduate Education (EngAGE), diversity recruitment Lecture on Graduate Education and Research	17, 2018
Society of Women Engineers, Faculty Panel on Research and Career Opportunities	2017
Educational Outreach Video, <u>Is Moore's Law Ending?</u>	2017
Society of Women Engineers, Engineering Exploration Experience, <i>Electricity from our Bare Hands</i>	2017
GOALS (Greater Opportunities Advancing Leadership and Science) for Girls	2016
Society of Women Engineers, Engineering Exploration Experience, How Computer Chips Work	2016
MakeCU Hardware Hackathon, How to Hack Like An Engineer	2016
Science & Engineering Expo at the School at Columbia, How to Make Computer Chips	2016
Society of Women Engineering, Panel on Undergraduate Research	2015
MIT+K12 Videos, What is a Semiconductor?	2015
Video creator and actor, Engaging, entertaining, and educational STEM video with 400,000 views	
MIT+K12 Videos, <u>How Computers Compute</u>	2014
Video creator and actor, Engaging, entertaining, and educational STEM video with 35,000 views	
MIT Online Science, Technology, and Engineering Community (MOSTEC) Guest lecturer, STEM enrichment lecture to inspire underserved high school seniors	3, 2014
MIT Educational Studies Program, Spark	2013
Teacher, taught Saturday classes to ~100 students middle school students on computer chip fabrication	on
MIT Minority Introduction to Engineering and Science (MITES) Guest lecturer, STEM program serving under-represented high school juniors	2012
MIT+K12 and Khan Academy, <u>Series and Parallel Circuits: A Water Analogy</u> Video and experiment creator and actor, demonstration of different types of circuits with 16,000 view	2012 vs
Cambridge Science Festival IDEAS Competition Mentor, advised team in local green technologies competition	2012
MIT Society of Women Engineers, Women in Science & Engineering Program (WiSE) Guest lecturer, STEM outreach to inspire young women	2012

MIT Society of Women Engineers, Keys to Empowering Youth

Guest lecturer, engineering outreach to middle school girls

University of Texas, UTeach Outreach

Teacher, taught a weekly hands-on science unit to four local elementary school classrooms

University of Texas, Student Engineers Educating Kids (SEEK)

Mentor, academic weekly mentor to students from disadvantaged middle schools